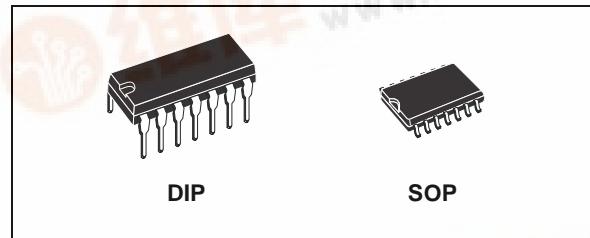




**HCF4023B**

## TRIPLE 3 INPUT NAND GATE

- PROPAGATION DELAY TIME :  
 $t_{PD} = 60\text{ns}$  (Typ.) at  $V_{DD} = 10\text{V}$
  - BUFFERED INPUTS AND OUTPUTS
  - STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
  - QUIESCENT CURRENT SPECIFIED UP TO 20V
  - 5V, 10V AND 15V PARAMETRIC RATINGS
  - INPUT LEAKAGE CURRENT  
 $I_I = 100\text{nA}$  (MAX) AT  $V_{DD} = 18\text{V}$   $T_A = 25^\circ\text{C}$
  - 100% TESTED FOR QUIESCENT CURRENT
  - MEETS ALL REQUIREMENTS OF JEDEC JESD13B " STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



## **ORDER CODES**

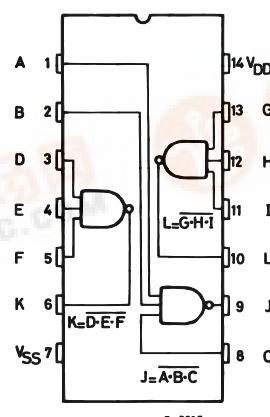
PACKAGE	TUBE	T & R
DIP	HCF4023BEY	
SOP	HCF4023BM1	HCF4023M013TR

implementation of the NAND function and supplement the existing family of CMOS gates. All inputs and outputs are buffered.

## **DESCRIPTION**

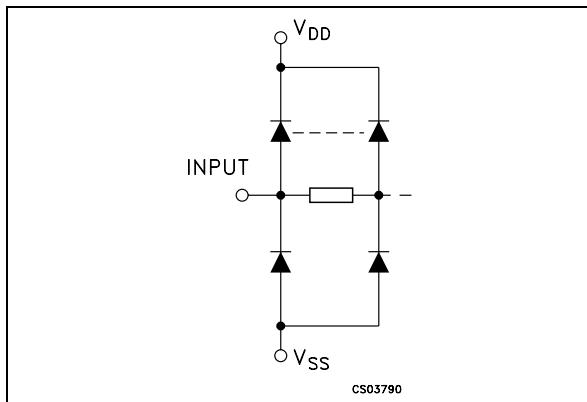
The HCF4023B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. The HCF4023B TRIPLE 3 INPUT NAND GATE provides the system designer with direct

## PIN CONNECTION

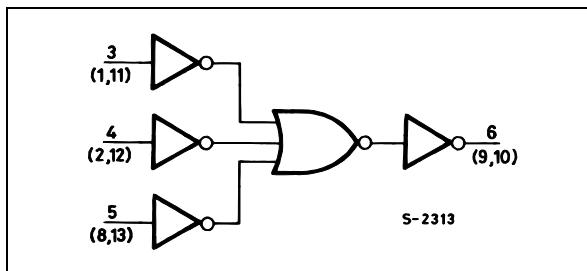


## HCF4023B

### INPUT EQUIVALENT CIRCUIT



### LOGIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	Supply Voltage	-0.5 to +22	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>DD</sub> + 0.5	V
I <sub>I</sub>	DC Input Current	± 10	mA
P <sub>D</sub>	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T <sub>op</sub>	Operating Temperature	-55 to +125	°C
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V<sub>SS</sub> pin voltage.

### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V <sub>DD</sub>	Supply Voltage	3 to 20	V
V <sub>I</sub>	Input Voltage	0 to V <sub>DD</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value						Unit	
		$V_I$ (V)	$V_O$ (V)	$ I_{OL} $ ( $\mu$ A)	$V_{DD}$ (V)	$T_A = 25^\circ C$			$-40 \text{ to } 85^\circ C$		$-55 \text{ to } 125^\circ C$		
						Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
$I_L$	Quiescent Current	0/5			5		0.01	0.25		7.5		7.5	$\mu A$
		0/10			10		0.01	0.5		15		15	
		0/15			15		0.01	1		30		30	
		0/20			20		0.02	5		150		150	
$V_{OH}$	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
$V_{OL}$	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
$V_{IH}$	High Level Input Voltage		0.5/4.5	<1	5	3.5			3.5		3.5		V
			1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
$V_{IL}$	Low Level Input Voltage		4.5/0.5	<1	5			1.5		1.5		1.5	V
			9/1	<1	10			3		3		3	
			13.5/1.5	<1	15			4		4		4	
$I_{OH}$	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.1		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
$I_{OL}$	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
$I_I$	Input Leakage Current	0/18	Any Input		18		$\pm 10^{-5}$	$\pm 0.1$		$\pm 1$		$\pm 1$	$\mu A$
$C_I$	Input Capacitance		Any Input				5	7.5					pF

The Noise Margin for both "1" and "0" level is: 1V min. with  $V_{DD}=5V$ , 2V min. with  $V_{DD}=10V$ , 2.5V min. with  $V_{DD}=15V$

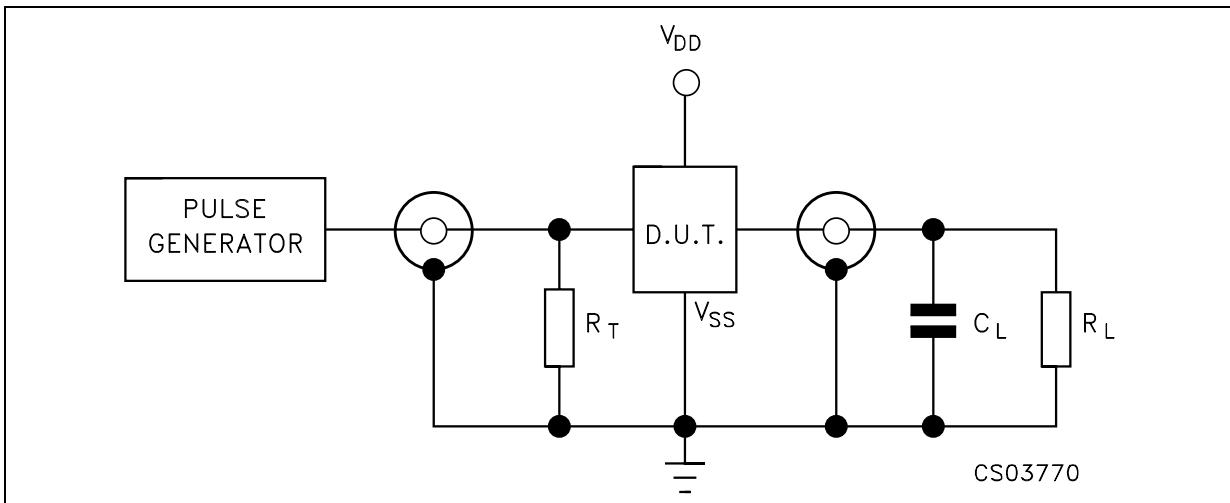
DYNAMIC ELECTRICAL CHARACTERISTICS ( $T_{amb} = 25^\circ C$ ,  $C_L = 50pF$ ,  $R_L = 200K\Omega$ ,  $t_r = t_f = 20 \text{ ns}$ )

Symbol	Parameter	Test Condition				Value (*)			Unit	
		$V_{DD}$ (V)				Min.	Typ.	Max.		
$t_{PLH} t_{PHL}$	Propagation Delay Time	5						125	250	ns
		10						60	120	
		15						45	90	
$t_{TLH} t_{THL}$	Output Transition Time	5						100	200	ns
		10						50	100	
		15						40	80	

(\*) Typical temperature coefficient for all  $V_{DD}$  value is 0.3 %/ $^\circ C$ .

## HCF4023B

### TEST CIRCUIT

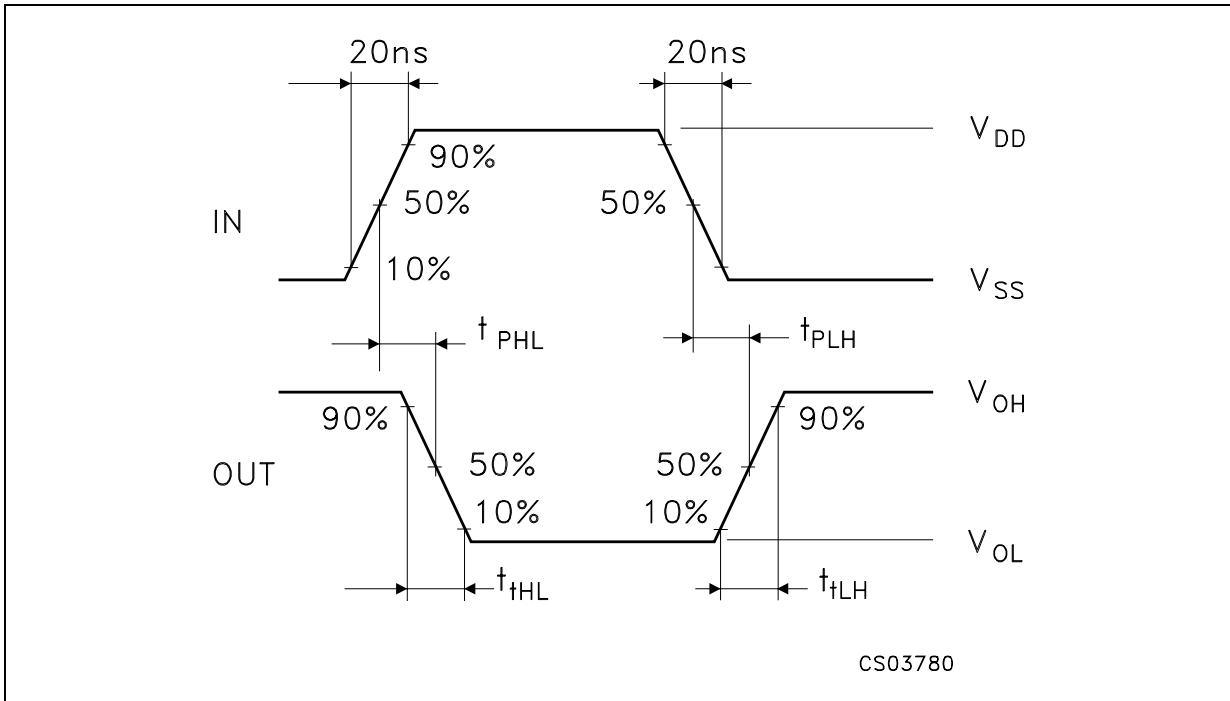


$C_L = 50\text{pF}$  or equivalent (includes jig and probe capacitance)

$R_L = 200\text{K}\Omega$

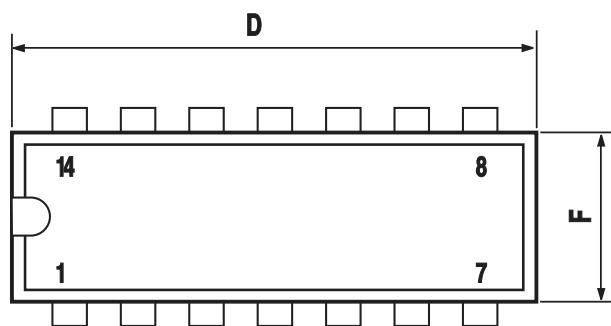
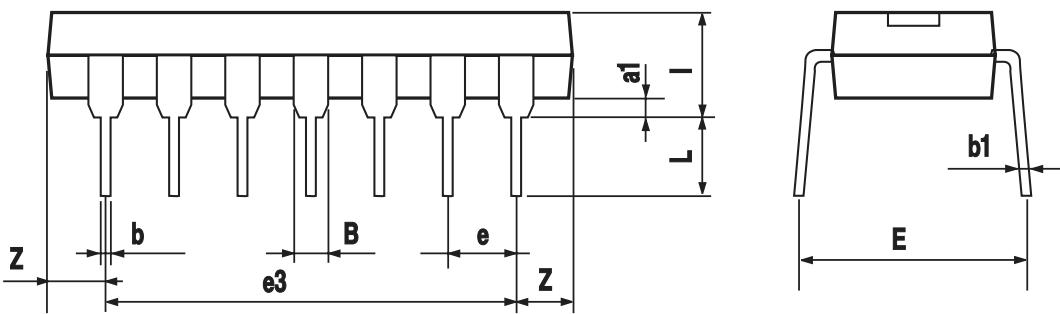
$R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

### WAVEFORM : PROPAGATION DELAY TIMES (f=1MHz; 50% duty cycle)



### Plastic DIP-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100

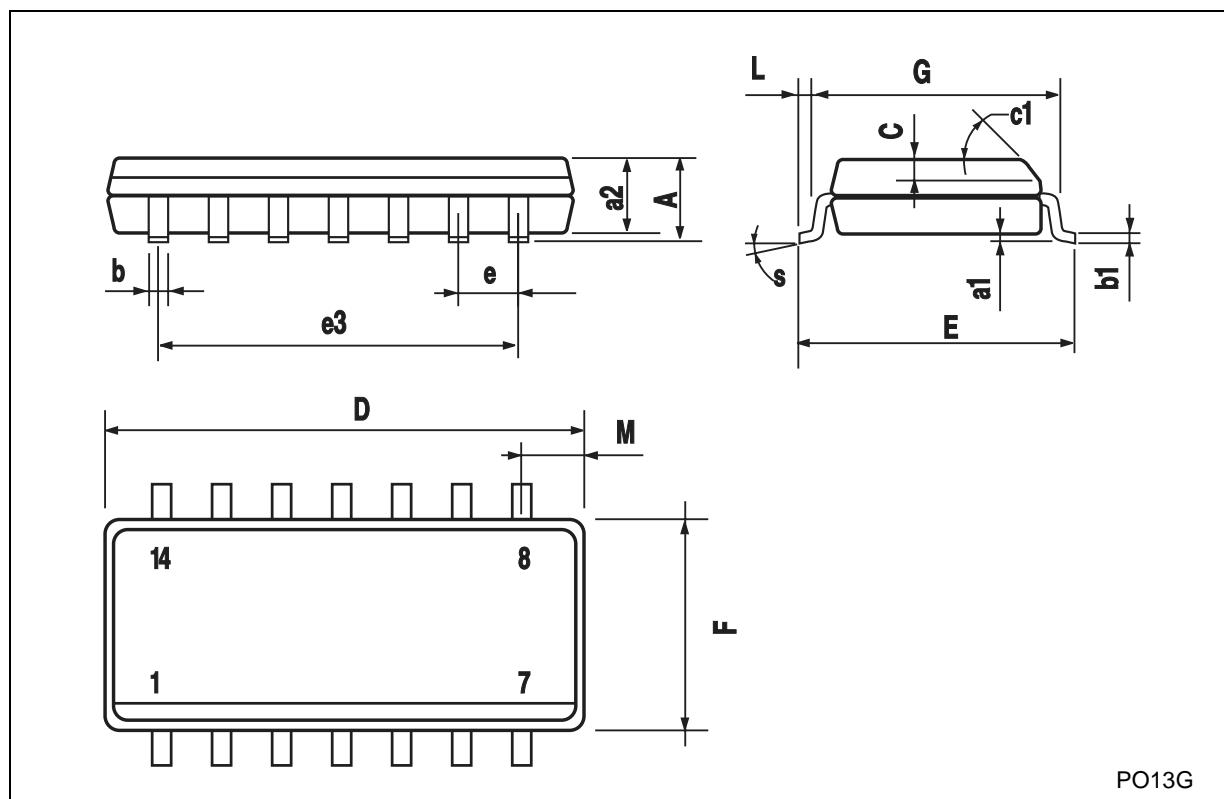


P001A

## HCF4023B

### SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



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